

# ESD Protection diode

RSB6.8CS

●Application

ESD Protection, bi direction

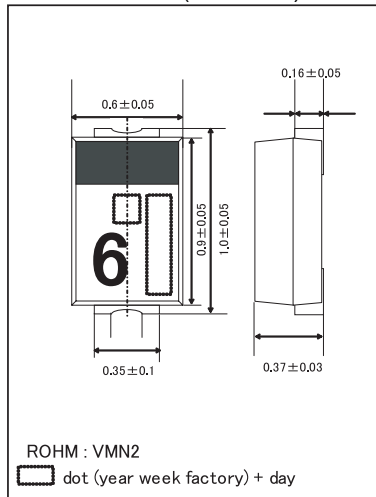
●Features

- 1) Ultra small mold type. (VMN2)
- 2) High reliability.
- 3) Bi chip-mounter, automatic mounting is possible.

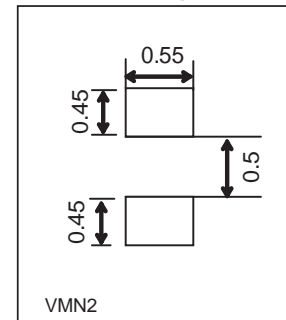
●Construction

Silicon epitaxial planar

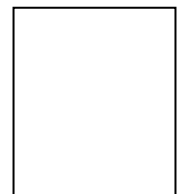
●Dimensions (Unit : mm)



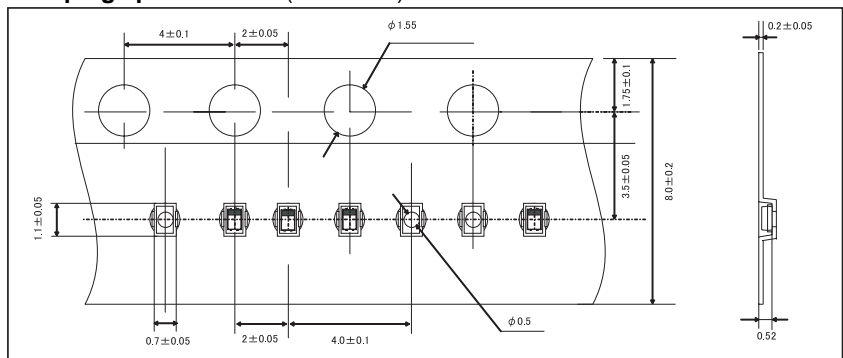
●Land size figure (Unit : mm)



●Structure



●Taping specifications (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak pulse power (tp=10×1000us)	Ppk	10	W
Power dissipation	P	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
Operating temperature	Topor	-55 to +150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Zener voltage	Vz	5.78	-	7.82	V	Iz=1mA
Reverse current	IR	-	-	0.5	μA	VR=3.5V
Capacitance between terminals	Ct	-	15	-	pF	VR=0V, f=1MHz